

## 5 A - 1200 V - low drop internally clamped IGBT

### Features

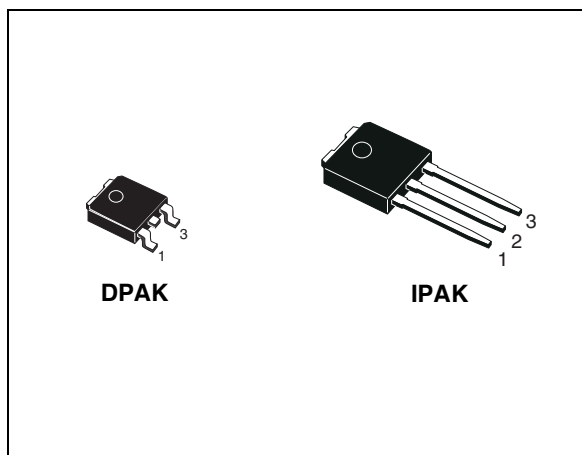
- Low on-voltage drop ( $V_{CE(sat)}$ )
- High current capability
- Off losses include tail current
- High voltage clamping

### Applications

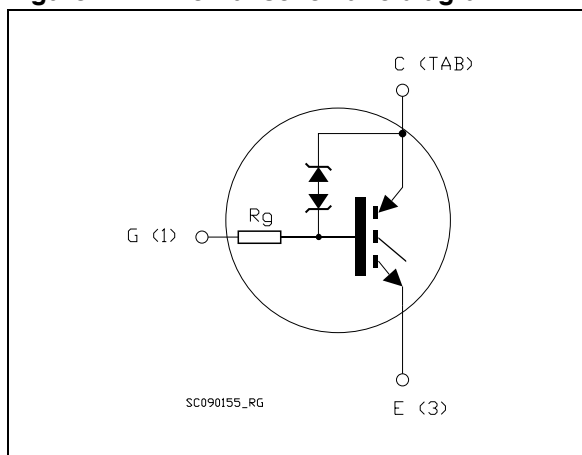
- Light dimmer
- Inrush current limitation
- Pre-heating for electronic lamp ballast

### Description

This IGBT utilizes the advanced Power MESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

| Order codes    | Marking    | Package | Packaging     |
|----------------|------------|---------|---------------|
| STGD5NB120SZ-1 | GD5NB120SZ | IPAK    | Tube          |
| STGD5NB120SZT4 | GD5NB120SZ | DPAK    | Tape and reel |

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

| Symbol         | Parameter                                               | Value       | Unit |
|----------------|---------------------------------------------------------|-------------|------|
| $V_{CES}$      | Collector-emitter voltage ( $V_{GE} = 0$ )              | 1200        | V    |
| $I_C^{(1)}$    | Collector current (continuous) at $T_C = 25\text{ °C}$  | 10          | A    |
| $I_C^{(1)}$    | Collector current (continuous) at $T_C = 100\text{ °C}$ | 5           | A    |
| $I_{CP}^{(2)}$ | Pulsed collector current                                | 10          | A    |
| $I_{CL}^{(3)}$ | Turn-off latching current                               | 10          | A    |
| $V_{GE}$       | Gate-emitter voltage                                    | ±20         | V    |
| $V_{ECR}$      | Emitter-collector voltage                               | 20          | V    |
| $E_{AS}^{(4)}$ | Single pulse avalanche energy at $T_C = 25\text{ °C}$   | 10          | mJ   |
|                | Single pulse avalanche energy at $T_C = 100\text{ °C}$  | 7           | mJ   |
| $P_{TOT}$      | Total dissipation at $T_C = 25\text{ °C}$               | 75          | W    |
| $T_j$          | Operating junction temperature                          | – 55 to 150 | °C   |

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. Pulse width limited by max. temperature allowed

3.  $V_{CLAMP} = 80\% (V_{CES})$ ,  $V_{GE} = 15\text{ V}$ ,  $R_G = 10\text{ }\Omega$ ,  $T_J = 150\text{ °C}$

4.  $V_{CE} = 50\text{ V}$ ,  $I_{AV} = 3.3\text{ A}$

**Table 3. Thermal resistance**

| Symbol         | Parameter                                 | Value | Unit |
|----------------|-------------------------------------------|-------|------|
| $R_{thj-case}$ | Thermal resistance junction-case IGBT max | 1.67  | °C/W |
| $R_{thj-amb}$  | Thermal resistance junction-ambient max   | 100   | °C/W |

## 2 Electrical characteristics

( $T_{CASE}=25\text{ }^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Static electrical characteristics**

| Symbol        | Parameter                                            | Test conditions                                                                                                                  | Min. | Typ.       | Max.      | Unit                           |
|---------------|------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------|------|------------|-----------|--------------------------------|
| $V_{(BR)CES}$ | Collector-emitter breakdown voltage ( $V_{GE} = 0$ ) | $I_C = 10\text{ mA}$                                                                                                             | 1200 |            |           | V                              |
| $V_{CE(sat)}$ | Collector-emitter saturation voltage                 | $V_{GE} = 15\text{ V}$ , $I_C = 5\text{ A}$<br>$V_{GE} = 15\text{ V}$ , $I_C = 5\text{ A}$ , $T_C = 125\text{ }^{\circ}\text{C}$ |      | 1.3<br>1.2 | 2.0       | V<br>V                         |
| $V_{GE(th)}$  | Gate threshold voltage                               | $V_{CE} = V_{GE}$ , $I_C = 250\text{ }\mu\text{A}$                                                                               | 2    |            | 5         | V                              |
| $V_{GE}$      | Gate emitter voltage                                 | $V_{CE} = 2.5\text{ V}$ , $I_C = 2\text{ A}$ ,<br>$T_C = 25 \div 125\text{ }^{\circ}\text{C}$                                    |      |            | 6.5       | V                              |
| $I_{CES}$     | Collector cut-off current ( $V_{GE} = 0$ )           | $V_{CE} = 900\text{ V}$<br>$V_{CE} = 900\text{ V}$ , $T_C = 125\text{ }^{\circ}\text{C}$                                         |      |            | 50<br>250 | $\mu\text{A}$<br>$\mu\text{A}$ |
| $I_{GES}$     | Gate-emitter leakage current ( $V_{CE} = 0$ )        | $V_{GE} = \pm 20\text{ V}$                                                                                                       |      |            | $\pm 100$ | nA                             |
| $g_{fs}$      | Forward transconductance                             | $V_{CE} = 15\text{ V}$ , $I_C = 5\text{ A}$                                                                                      |      | 5          |           | S                              |
| $R_G$         | Gate resistance                                      |                                                                                                                                  |      | 4          |           | k $\Omega$                     |

**Table 5. Dynamic electrical characteristics**

| Symbol    | Parameter                    | Test conditions                                               | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|---------------------------------------------------------------|------|------|------|------|
| $C_{ies}$ | Input capacitance            | $V_{CE} = 25\text{ V}$ , $f = 1\text{ MHz}$ ,<br>$V_{GE} = 0$ |      | 430  |      | pF   |
| $C_{oes}$ | Output capacitance           |                                                               |      | 40   |      | pF   |
| $C_{res}$ | Reverse transfer capacitance |                                                               |      | 7    |      | pF   |

**Table 6. Switching on/off (inductive load)**

| Symbol         | Parameter             | Test conditions                                                              | Min. | Typ. | Max. | Unit       |
|----------------|-----------------------|------------------------------------------------------------------------------|------|------|------|------------|
| $t_{d(on)}$    | Turn-on delay time    | $V_{CC} = 960\text{ V}$ , $I_C = 5\text{ A}$                                 |      | 690  |      | ns         |
| $t_r$          | Current rise time     | $R_{drive} = 1\text{ k}\Omega$ , $V_{GE} = 15\text{ V}$ ,<br>(see Figure 18) |      | 170  |      | ns         |
| $(di/dt)_{on}$ | Turn-on current slope |                                                                              |      | 39.6 |      | A/ $\mu$ s |
| $t_{d(on)}$    | Turn-on delay time    | $V_{CC} = 960\text{ V}$ , $I_C = 5\text{ A}$                                 |      | 600  |      | ns         |
| $t_r$          | Current rise time     | $R_{drive} = 1\text{ k}\Omega$ , $V_{GE} = 15\text{ V}$                      |      | 185  |      | ns         |
| $(di/dt)_{on}$ | Turn-on current slope | $T_C = 125\text{ }^\circ\text{C}$ (see Figure 18)                            |      | 39   |      | A/ $\mu$ s |
| $t_c$          | Cross-over time       | $V_{CC} = 960\text{ V}$ , $I_C = 5\text{ A}$                                 |      | 4    |      | $\mu$ s    |
| $t_r(V_{off})$ | Off voltage rise time | $R_{drive} = 1\text{ k}\Omega$ , $V_{GE} = 15\text{ V}$                      |      | 2.2  |      | $\mu$ s    |
| $t_{d(off)}$   | Turn-off delay time   | (see Figure 18)                                                              |      | 12.1 |      | $\mu$ s    |
| $t_f$          | Current fall time     |                                                                              |      | 1.13 |      | $\mu$ s    |
| $t_c$          | Cross-over time       | $V_{CC} = 960\text{ V}$ , $I_C = 5\text{ A}$                                 |      | 5    |      | $\mu$ s    |
| $t_r(V_{off})$ | Off voltage rise time | $R_{drive} = 1\text{ k}\Omega$ , $V_{GE} = 15\text{ V}$ ,                    |      | 2.2  |      | $\mu$ s    |
| $t_{d(off)}$   | Turn-off delay time   | $T_C = 125\text{ }^\circ\text{C}$ (see Figure 18)                            |      | 12.1 |      | $\mu$ s    |
| $t_f$          | Current fall time     |                                                                              |      | 2    |      | $\mu$ s    |

**Table 7. Switching energy (inductive load)**

| Symbol          | Parameter                 | Test conditions                                           | Min. | Typ.  | Max. | Unit |
|-----------------|---------------------------|-----------------------------------------------------------|------|-------|------|------|
| $E_{on}^{(1)}$  | Turn-on switching losses  | $V_{CC} = 960\text{ V}$ , $I_C = 5\text{ A}$              |      | 2.59  |      | mJ   |
| $E_{off}^{(2)}$ | Turn-off switching losses | $R_{drive} = 1\text{ k}\Omega$ , $V_{GE} = 15\text{ V}$   |      | 9     |      | mJ   |
| $E_{ts}$        | Total switching losses    | (see Figure 18)                                           |      | 11.59 |      | mJ   |
| $E_{on}^{(1)}$  | Turn-on switching losses  | $V_{CC} = 960\text{ V}$ , $I_C = 5\text{ A}$              |      | 2.64  |      | mJ   |
| $E_{off}^{(2)}$ | Turn-off switching losses | $R_{drive} = 1\text{ k}\Omega$ , $V_{GE} = 15\text{ V}$ , |      | 10.2  |      | mJ   |
| $E_{ts}$        | Total switching losses    | $T_C = 125\text{ }^\circ\text{C}$ (see Figure 18)         |      | 12.68 |      | mJ   |

1.  $E_{on}$  is the turn-on losses when a typical diode is used in the test circuit in (see Figure 18). If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs & Diode are at the same temperature ( $25^\circ\text{C}$  and  $125^\circ\text{C}$ )

2. Turn-off losses include also the tail of the collector current

**Table 8. Functional test**

| Symbol   | Parameter                             | Test conditions                                                                                                         | Min. | Typ. | Max. | Unit |
|----------|---------------------------------------|-------------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| $I_{AS}$ | Unclamped inductive switching current | $V_{CC} = 50\text{ V}$ , $L = 1.8\text{ mH}$<br>$T_{start} = 25\text{ }^\circ\text{C}$ , $R_{drive} = 1\text{ k}\Omega$ | 3.3  |      |      | A    |

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

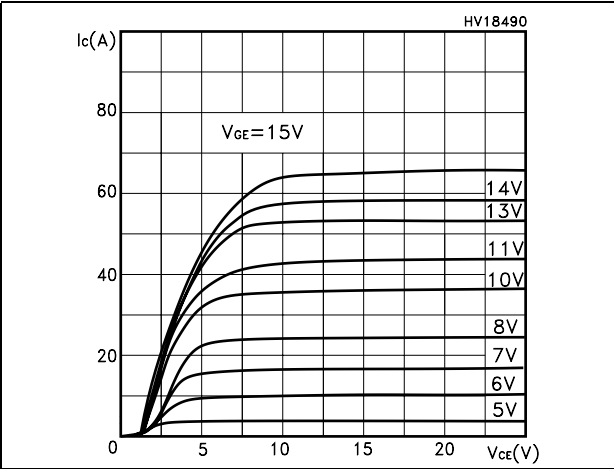


Figure 3. Transfer characteristics

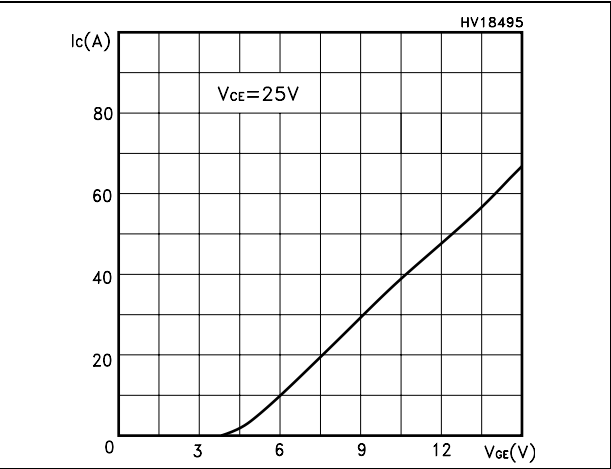


Figure 4. Transconductance

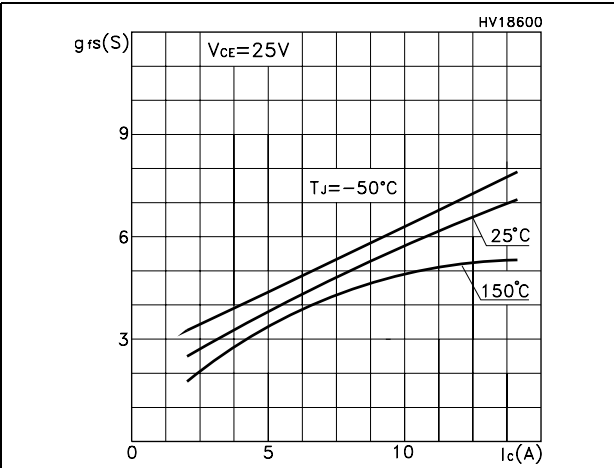


Figure 5. Collector-emitter on voltage vs temperature

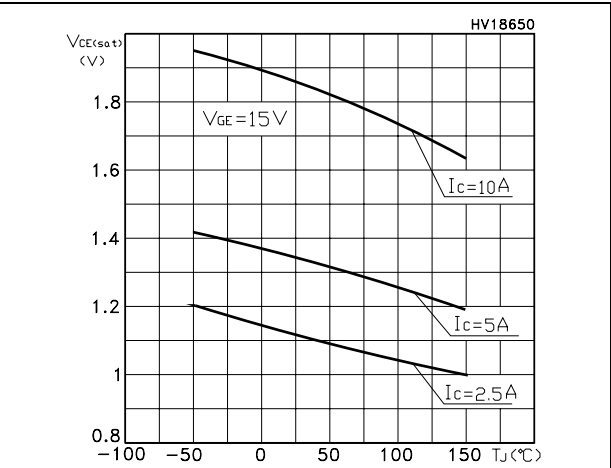


Figure 6. Gate charge vs gate-source voltage

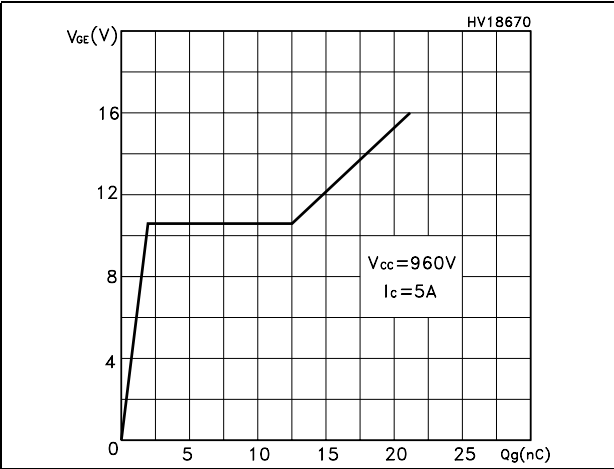


Figure 7. Capacitance variations

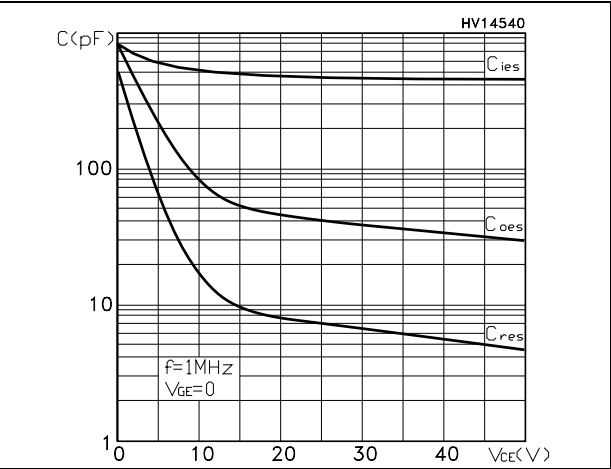


Figure 8. Normalized gate threshold voltage vs temperature

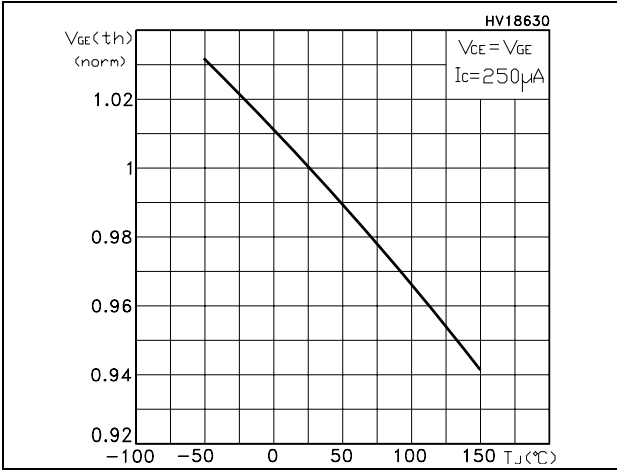


Figure 9. Collector-emitter on voltage vs collector current

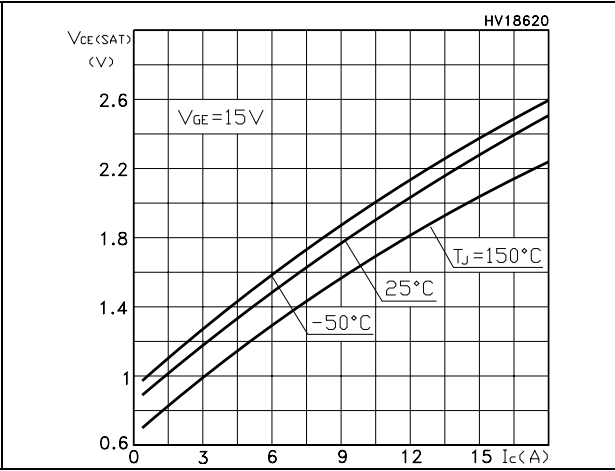


Figure 10. Breakdown voltage vs temperature

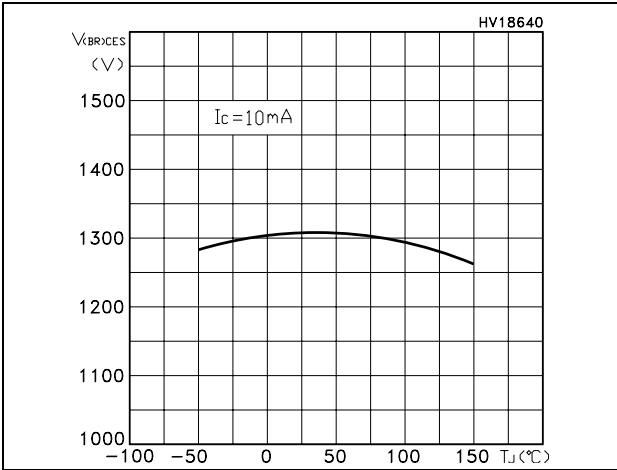


Figure 11. Normalized collector-emitter on voltage vs temperature

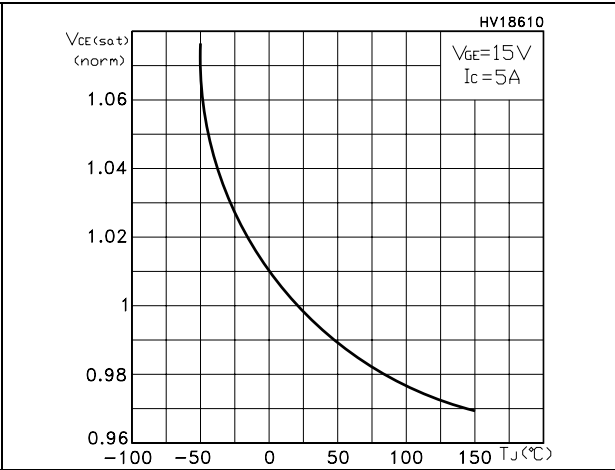


Figure 12. Switching losses vs gate resistance

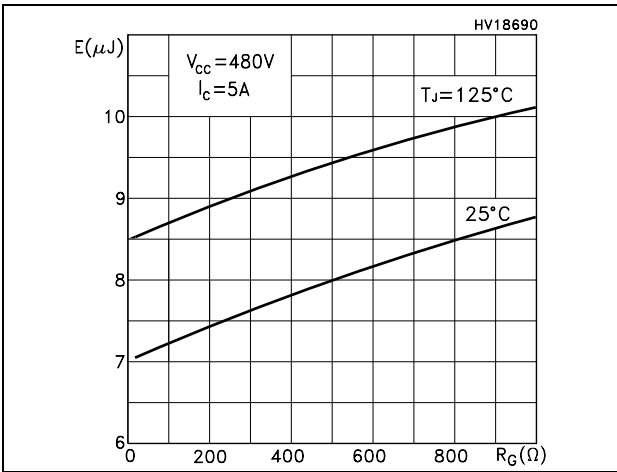


Figure 13. Switching losses vs collector current

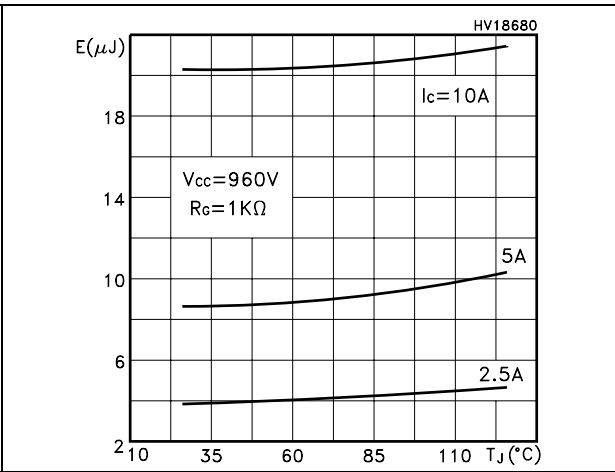


Figure 14. Turn-off SOA

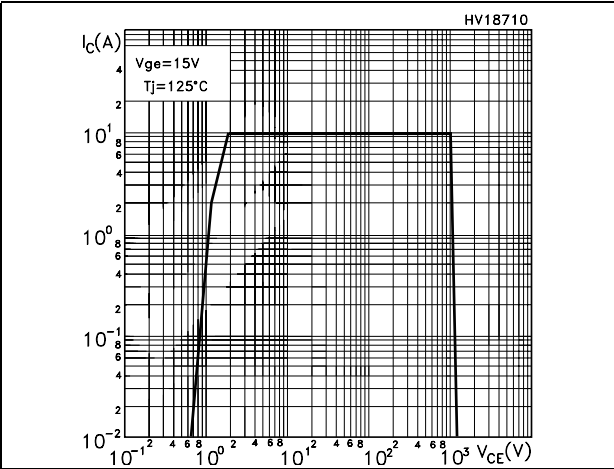
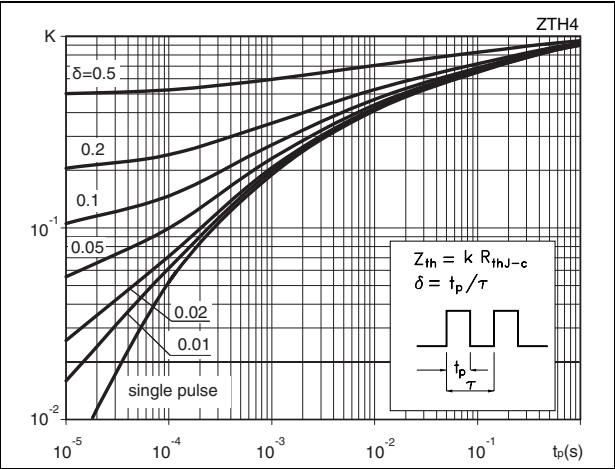


Figure 15. Thermal impedance



3 Test circuit

Figure 16. Test circuit for inductive load switching

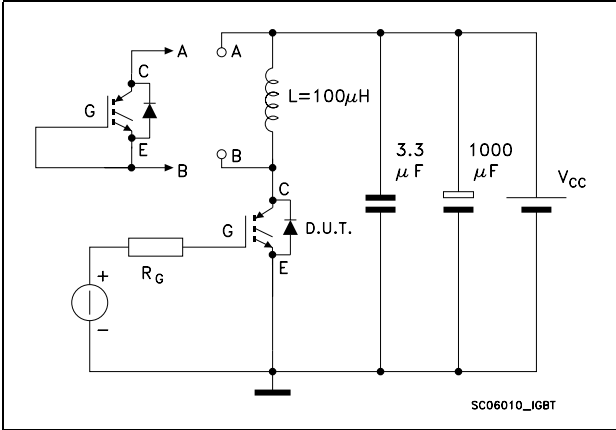


Figure 17. Gate charge test circuit

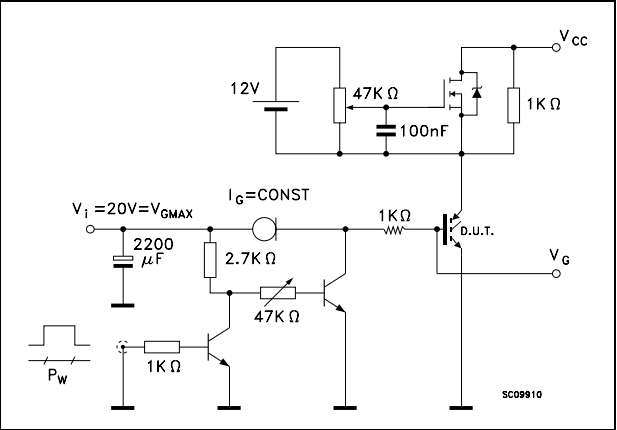
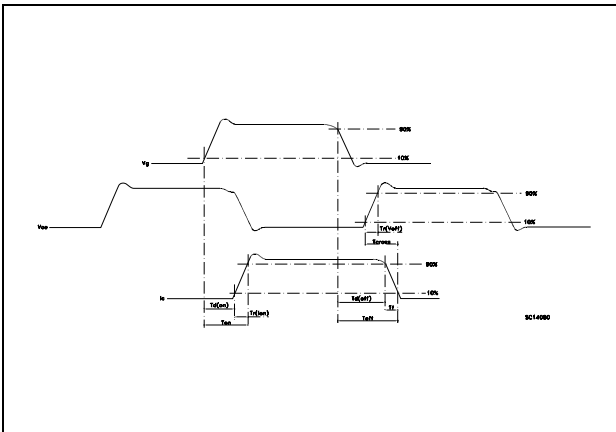


Figure 18. Switching waveform

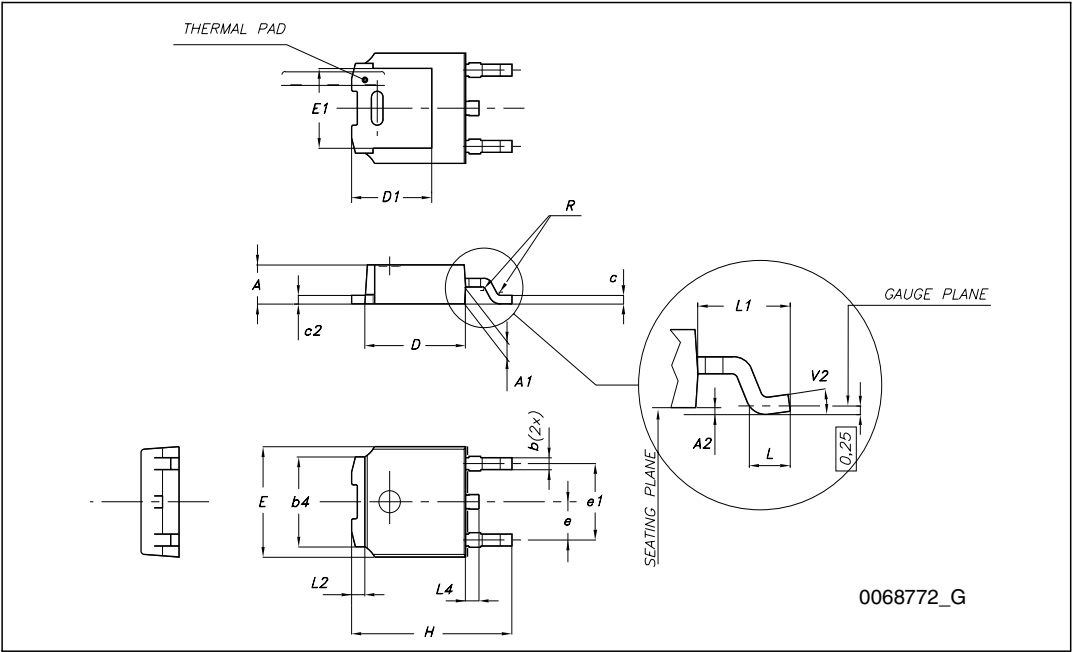


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

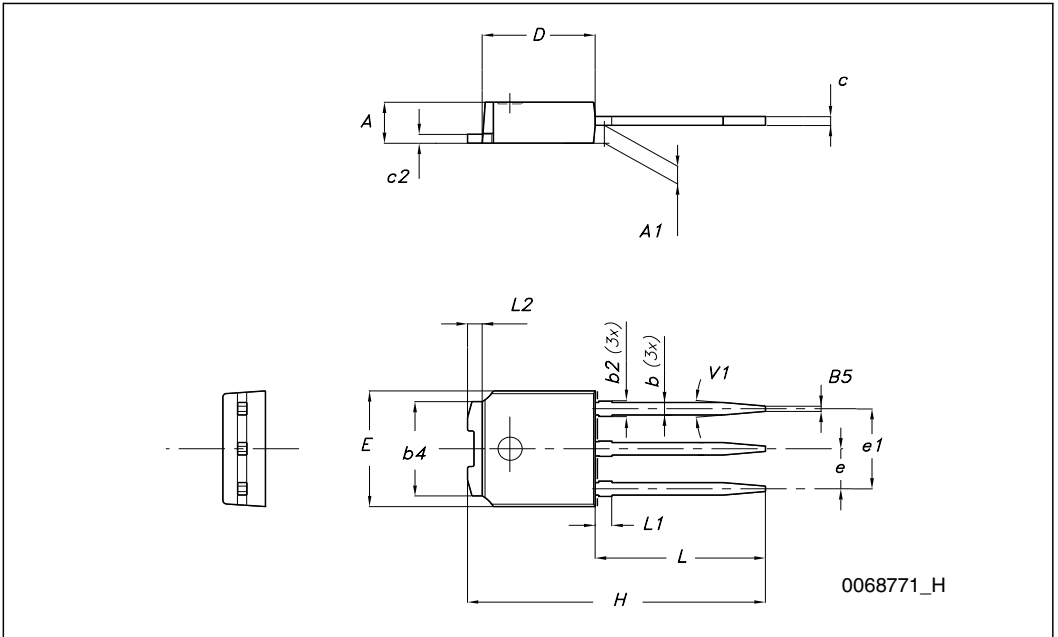
TO-252 (DPAK) mechanical data

| DIM. | mm.  |      |       |
|------|------|------|-------|
|      | min. | typ  | max.  |
| A    | 2.20 |      | 2.40  |
| A1   | 0.90 |      | 1.10  |
| A2   | 0.03 |      | 0.23  |
| b    | 0.64 |      | 0.90  |
| b4   | 5.20 |      | 5.40  |
| c    | 0.45 |      | 0.60  |
| c2   | 0.48 |      | 0.60  |
| D    | 6.00 |      | 6.20  |
| D1   |      | 5.10 |       |
| E    | 6.40 |      | 6.60  |
| E1   |      | 4.70 |       |
| e    |      | 2.28 |       |
| e1   | 4.40 |      | 4.60  |
| H    | 9.35 |      | 10.10 |
| L    | 1    |      |       |
| L1   |      | 2.80 |       |
| L2   |      | 0.80 |       |
| L4   | 0.60 |      | 1     |
| R    |      | 0.20 |       |
| V2   | 0°   |      | 8°    |



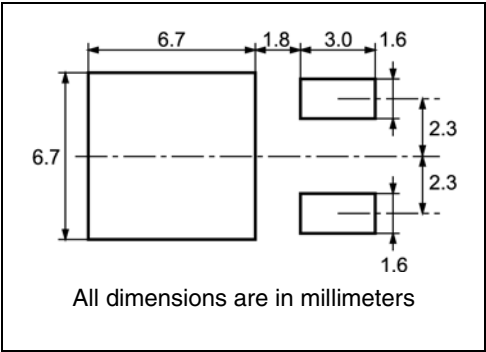
TO-251 (IPAK) mechanical data

| DIM. | mm.  |       |      |
|------|------|-------|------|
|      | min. | typ   | max. |
| A    | 2.20 |       | 2.40 |
| A1   | 0.90 |       | 1.10 |
| b    | 0.64 |       | 0.90 |
| b2   |      |       | 0.95 |
| b4   | 5.20 |       | 5.40 |
| c    | 0.45 |       | 0.60 |
| c2   | 0.48 |       | 0.60 |
| D    | 6.00 |       | 6.20 |
| E    | 6.40 |       | 6.60 |
| e    |      | 2.28  |      |
| e1   | 4.40 |       | 4.60 |
| H    |      | 16.10 |      |
| L    | 9.00 |       | 9.40 |
| (L1) | 0.80 |       | 1.20 |
| L2   |      | 0.80  |      |
| V1   |      | 10 °  |      |

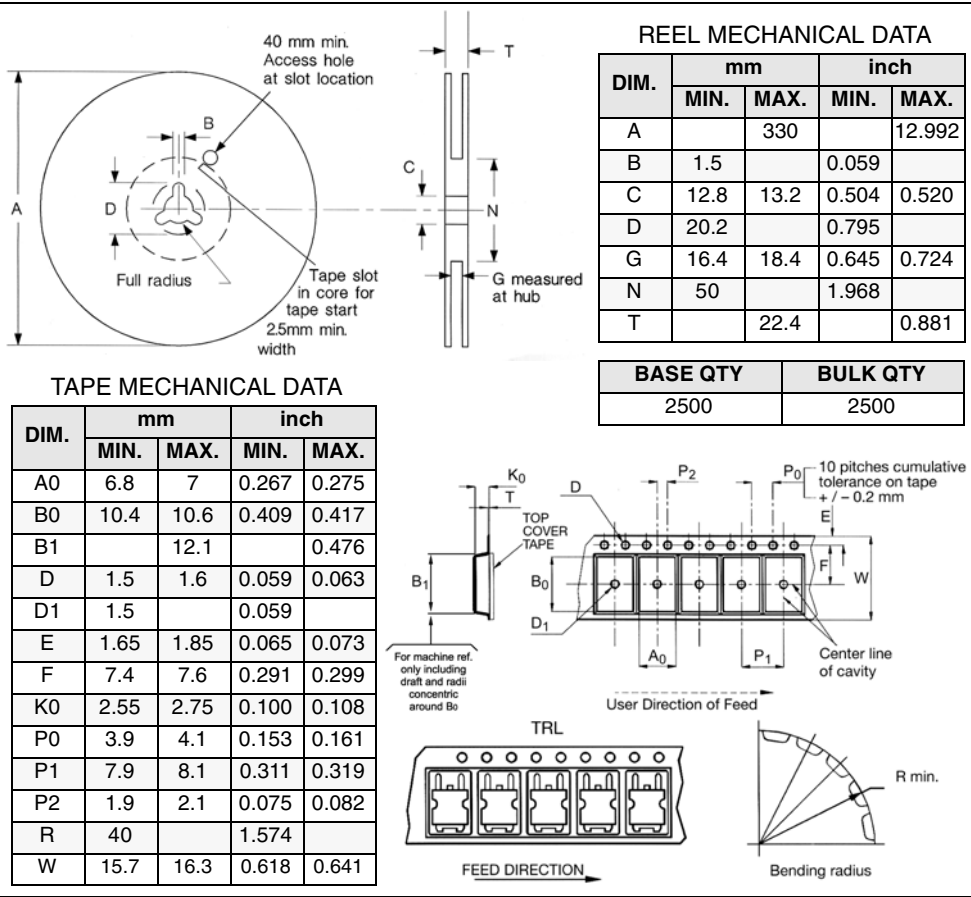


# 5 Packaging mechanical data

## DPAK FOOTPRINT



## TAPE AND REEL SHIPMENT



## 6 Revision history

**Table 9. Document revision history**

| Date        | Revision | Changes                                                               |
|-------------|----------|-----------------------------------------------------------------------|
| 06-Oct-2003 | 5        | No history because migration                                          |
| 18-Jan-2005 | 6        | Final datasheet                                                       |
| 13-Nov-2008 | 7        | Insert new value in <a href="#">Table 2: Absolute maximum ratings</a> |

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